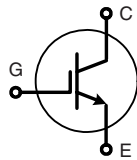


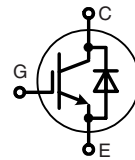
NPT³ IGBT

in miniBLOC package

I_{C25} = 100 A
V_{CES} = 1200 V
V_{CE(sat) typ.} = 2.1 V



IXEN 60N120

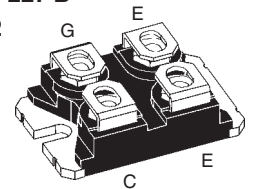


IXEN 60N120D1

miniBLOC, SOT-227 B



E153432



C = Collector
 G = Gate
 E = Emitter *

* Either Emitter terminal can be used as Main or Kelvin Emitter

IGBT

Symbol	Conditions	Maximum Ratings	
V _{CES}	T _{VJ} = 25°C to 150°C	1200	V
V _{GES}		± 20	V
I _{C25}	T _C = 25°C	100	A
I _{C90}	T _C = 90°C	65	A
I _{CM} V _{CEK}	V _{GE} = ±15 V; R _G = 22 Ω; T _{VJ} = 125°C RBSOA, Clamped inductive load; L = 100 μH	100	A
		V _{CES}	
t _{SC} (SCSOA)	V _{CE} = 900 V; V _{GE} = ±15 V; R _G = 22 Ω; T _{VJ} = 125°C non-repetitive	10	μs
P _{tot}	T _C = 25°C	445	W

Features

- NPT³ IGBT
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- optional HiPerFRED™ diode
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- miniBLOC package
 - isolated copper base plate
 - screw terminals
 - kelvin emitter terminal for easy drive
 - industry standard outline

Applications

- single switches
- choppers with complementary free wheeling diode
- phaselegs, H bridges, three phase bridges e.g. for
 - power supplies, UPS
 - AC, DC and SR drives
 - induction heating

Symbol	Conditions	Characteristic Values (T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _{CE(sat)}	I _C = 60 A; V _{GE} = 15 V; T _{VJ} = 25°C T _{VJ} = 125°C	2.1 2.5		V V	
V _{GE(th)}	I _C = 2 mA; V _{GE} = V _{CE}	4.5		6.5 V	
I _{CES}	V _{CE} = V _{CES} ; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C	0.8		0.8 mA mA	
I _{GES}	V _{CE} = 0 V; V _{GE} = ± 20 V			200 nA	
t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Inductive load, T _{VJ} = 125°C V _{CE} = 600 V; I _C = 60 A V _{GE} = ±15 V; R _G = 22 Ω		80 50 680 30	ns ns ns ns	
				7.2 4.8	mJ mJ
C _{ies}		V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		3.8	nF
Q _{Gon}		V _{CE} = 600 V; V _{GE} = 15 V; I _C = 50 A		350	nC
R _{thJC}					0.28 KW

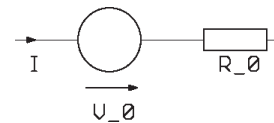
Diode (D1 version only)			
Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	110	A
I_{F90}	$T_C = 90^\circ\text{C}$	60	A

Characteristic Values
($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 60\text{ A}, V_{GE} = 0\text{ V}$	2.3	2.7	V
	$I_F = 60\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	1.7		V
I_{RM}	$I_F = 60\text{ A}, -di_F/dt = 500\text{ A}/\mu\text{s}, V_R = 600\text{ V}$	41		A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	200		ns
R_{thJC}			0.6	K/W

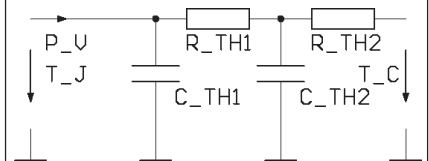
Component			
Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+150	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
M_D	mounting torque (M4)	1.5	Nm
	terminal connection torque (M4)	1.5	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{thCH}	with heatsink compound		0.1	K/W
Weight			30	g

Equivalent Circuits for Simulation
Conduction


IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 0.99\text{ V}; R_0 = 25\text{ m}\Omega$

Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.3\text{ V}; R_0 = 7\text{ m}\Omega$

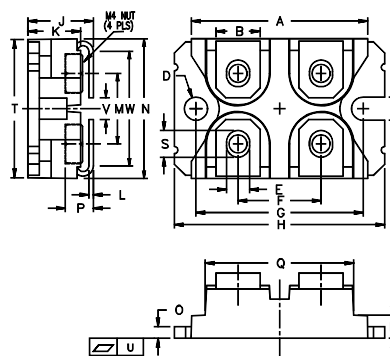
Thermal Response


IGBT (typ.)

$C_{th1} = 0.14\text{ J/K}; R_{th1} = 0.20\text{ K/W}$
 $C_{th2} = 0.91\text{ J/K}; R_{th2} = 0.08\text{ K/W}$

Diode (typ.)

$C_{th1} = 0.08\text{ J/K}; R_{th1} = 0.45\text{ K/W}$
 $C_{th2} = 0.54\text{ J/K}; R_{th2} = 0.15\text{ K/W}$

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

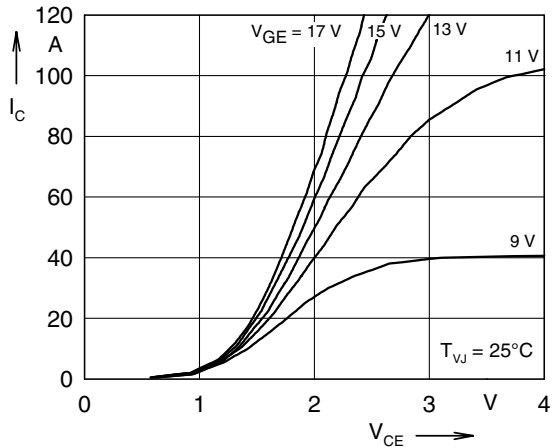


Fig. 1 Typ. output characteristics

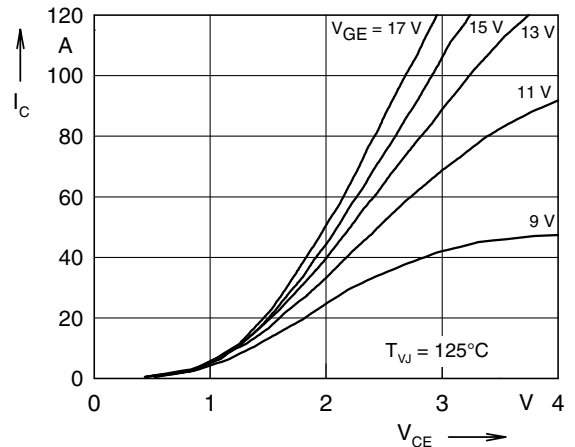


Fig. 2 Typ. output characteristics

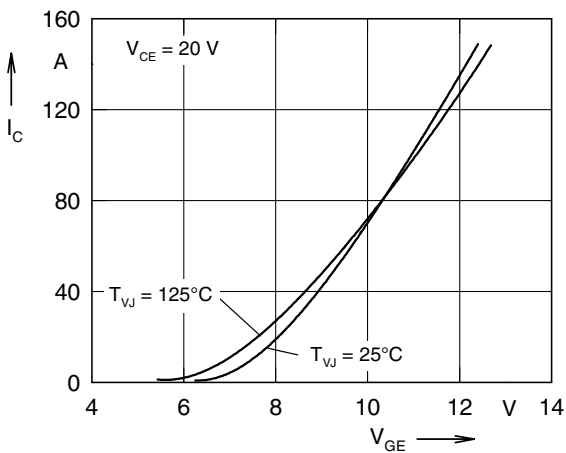


Fig. 3 Typ. transfer characteristics

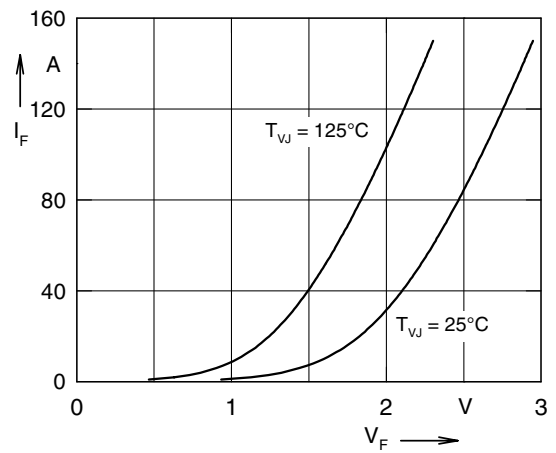


Fig. 4 Typ. forward characteristics of free wheeling diode

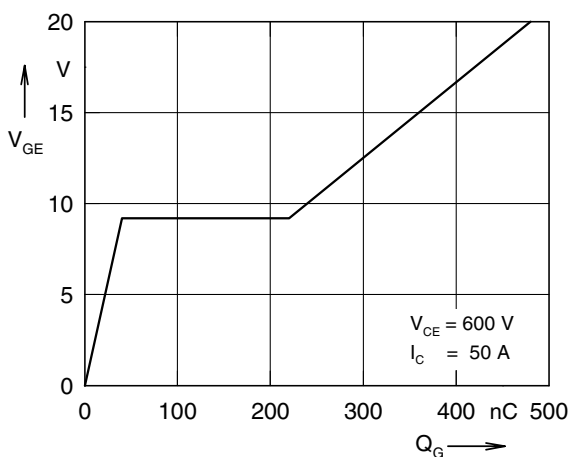


Fig. 5 Typ. turn on gate charge

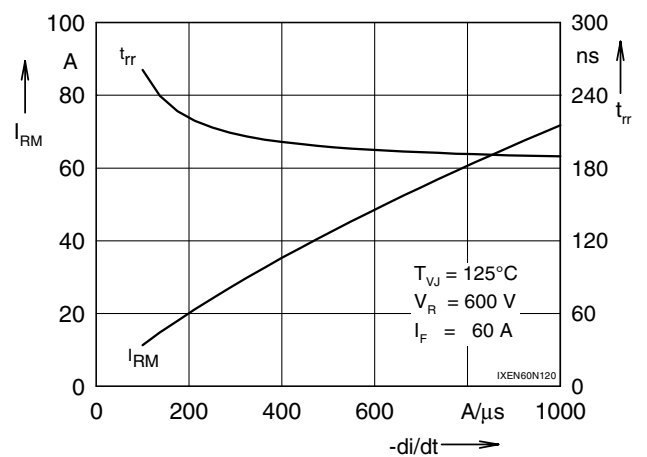


Fig. 6 Typ. turn off characteristics of free wheeling diode

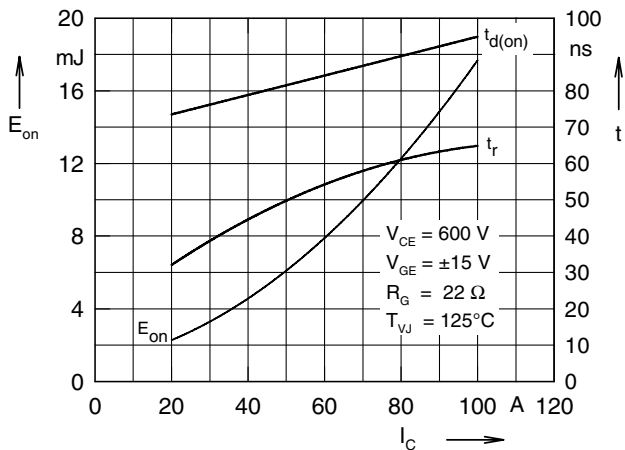


Fig. 7 Typ. turn on energy and switching times versus collector current

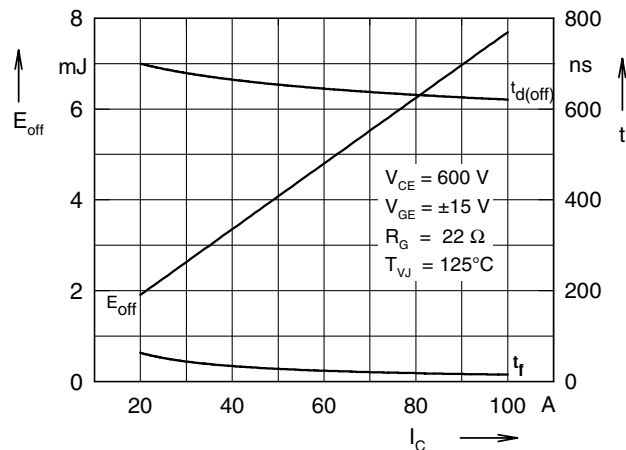


Fig. 8 Typ. turn off energy and switching times versus collector current

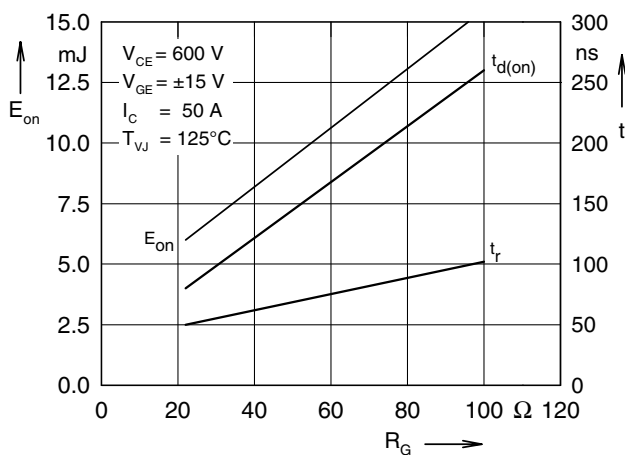


Fig. 9 Typ. turn on energy and switching times versus gate resistor

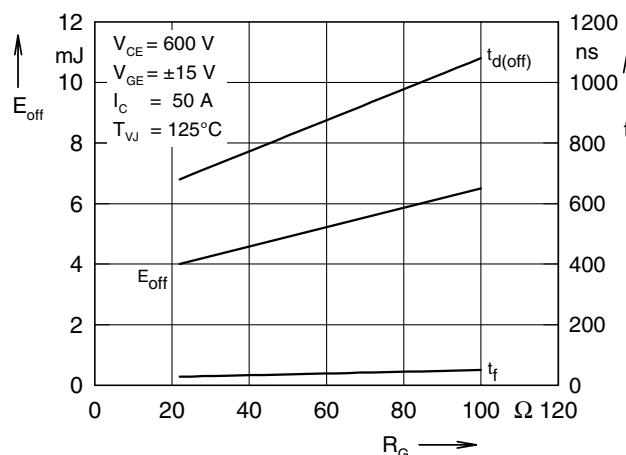


Fig. 10 Typ. turn off energy and switching times versus gate resistor

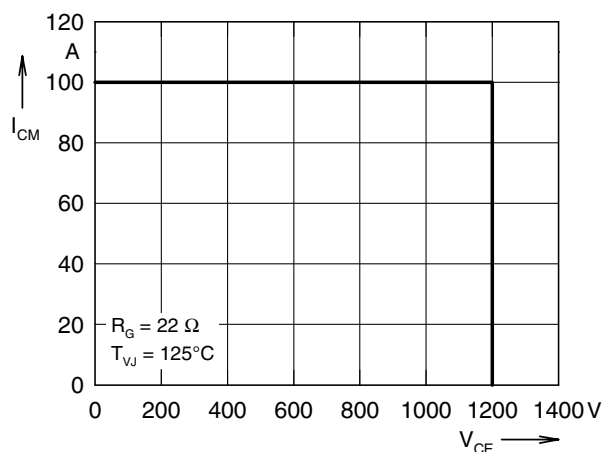


Fig. 11 Reverse biased safe operating area RBSOA

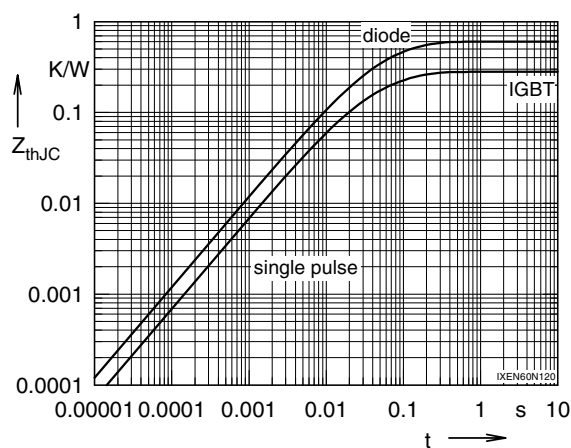


Fig. 12 Typ. transient thermal impedance